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(71) Applicant:

HYUNDAI ELECTRONICS IND. CO., LTD.

(72) Inventor:

CHOE, YANG-KYU

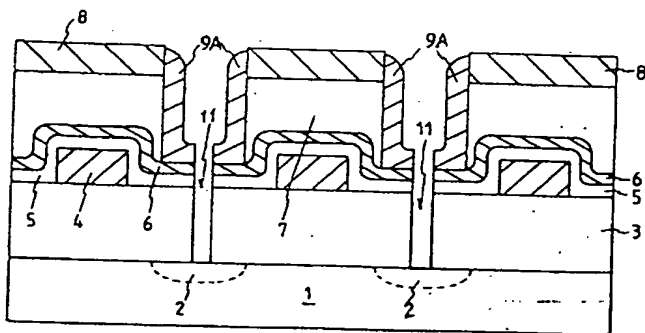
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(54) Title of Invention

METHOD OF FORMING MICRO CONTACT HOLE OF SEMICONDUCTOR DEVICE USING DOUBLE SPACE

Representative drawing


(57) Abstract:



The method comprises the steps of: forming N+/P+ active region (2), a first oxide insulating layer (3) on a silicon substrate (1) and patterning a metal layer for wiring (4); depositing a second oxide insulating layer and a first nitride insulating layer (6) along the upper of pattern of wired layer(4), spreading a third oxide insulating layer (7) and a first

polycrystalline silicon (8) on it; patterning the first polycrystalline silicon (8); depositing a second polycrystalline silicon (9) and a second nitride insulating layer (10) along the first polycrystalline silicon(8) the groove surface formed by dry-etching the third oxide insulating layer (7) ; forming a second nitride insulating layer spacer (10A) by blanket dry etch of the second nitride insulating layer(10); forming a second polycrystalline silicon spacer (9A) by blanket dry etch and forming a micro contact hole (11) by dry etching; removing the second nitride insulating layer spacer (10A) by wet etching.

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